



# 1N5400 thru 1N5408

**PLASTIC SILICON RECTIFIERS**      REVERSE VOLTAGE - **50 to 1000** Volts  
 FORWARD CURRENT - **3.0** Amperes

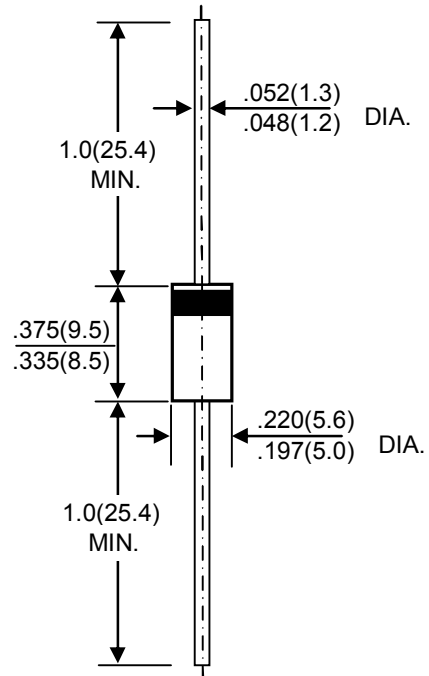
### FEATURES

- Low cost
- Diffused junction
- Low forward voltage drop
- Low reverse leakage current
- High current capability
- The plastic material carries UL recognition 94V-0

### MECHANICAL DATA

- Case: JEDEC DO-27 molded plastic
- Polarity: Color band denotes cathode
- Weight: 0.04 ounces , 1.1grams
- Mounting position: Any

### DO-27



Dimensions in inches and (millimeters)

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating at 25°C ambient temperature unless otherwise specified.

Single phase, half wave ,60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

CHARACTERISTICS	SYMBOL	1N 5400	1N 5401	1N 5402	1N 5403	1N 5404	1N 5405	1N 5406	1N 5407	1N 5408	UNIT
Maximum Recurrent Peak Reverse Voltage	VRRM	50	100	200	300	400	500	600	800	1000	V
Maximum RMS Voltage	VRMS	35	70	140	210	280	350	420	560	700	V
Maximum DC Blocking Voltage	VDC	50	100	200	300	400	500	600	800	1000	V
Maximum Average Forward Rectified Current @TA =55 °C	I(AV)	3.0									A
Peak Forward Surge Current 8.3ms Single Half Sine-Wave Supe Imposed on Rated Load(JEDEC Method)	IFSM	200									A
Maximum Forward Voltage at 3.0A DC	VF	1.0									V
Maximum DC Reverse Current @TJ=25°C at Rated DC Blocking Voltage @TJ=100°C	IR	5.0									µA
Typical Junction Capacitance (Note1)	CJ	50						35			pF
Typical Thermal Resistance (Note2)	RθJA	15									°C/W
Operating Temperature Range	TJ	-55 to +125									°C
Storage Temperature Range	TSTG	-55 to +150									°C

NOTES:1.Measured at 1.0 MHz and applied reverse voltage of 4.0V DC

2.Thermal resistance junction to ambient.

FIG. 1 – FORWARD CURRENT DERATING CURVE

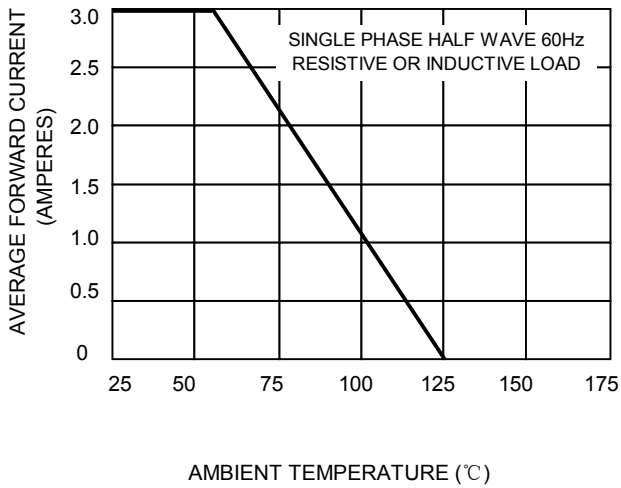


FIG. 2 – MAXIMUM NON-REPETITIVE SURGE CURRENT

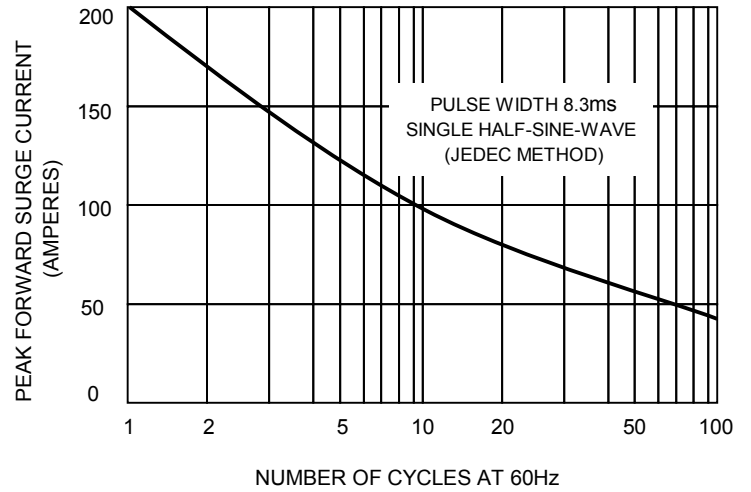


FIG.3 – TYPICAL JUNCTION CAPACITANCE

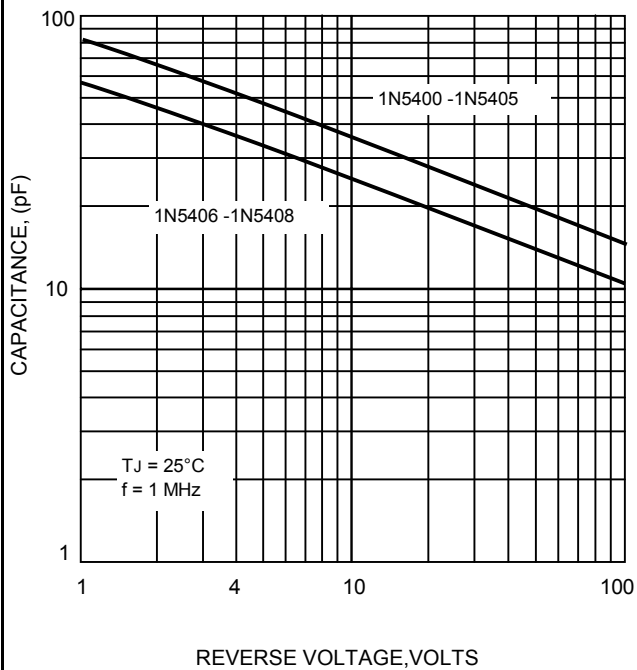


FIG.4-TYPICAL FORWARD CHARACTERISTICS

